

# Gusnu K Azhdarov

## List of Publications by Year in descending order

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17  
papers

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citations

1684188

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1474206

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docs citations

17  
times ranked

20  
citing authors

#	ARTICLE	IF	CITATIONS
1	Distribution of components in Ge-Si bulk single crystals grown under the continuous feeding of the melt with the second component (Si). Journal of Crystal Growth, 2001, 226, 437-442.	1.5	24
2	Distribution of aluminum and indium impurities in crystals of Ge-Si solid solutions grown from the melt. Crystallography Reports, 2006, 51, S192-S195.	0.6	12
3	Segregation of aluminum and indium impurities in Ge <sup>1-x</sup> Si <sup>x</sup> crystals. Inorganic Materials, 2007, 43, 3-7.	0.8	11
4	Growth of single crystals of semiconductor solid solutions by double feeding of the melt method. Crystallography Reports, 2010, 55, 716-719.	0.6	9
5	The distribution of Ga and Sb impurities in Ge-Si crystals grown by the Bridgman method using a feeding rod. Crystallography Reports, 2009, 54, 152-156.	0.6	8
6	Deep impurity levels in Ge <sup>1-x</sup> Si <sup>x</sup> alloys. Solid State Communications, 1999, 111, 675-679.	1.9	4
7	Growth of homogeneous single crystals of GeSi solid solutions using a Ge seed by the modified Bridgman method. Crystallography Reports, 2005, 50, S149-S151.	0.6	4
8	Hybrid technique for growing homogeneous single crystals of semiconductor solid solutions from melt. Crystallography Reports, 2014, 59, 442-445.	0.6	4
9	Negative Magnetoresistance in Indium Arsenide in the Extreme Quantum Limit. Physica Status Solidi (B): Basic Research, 1978, 87, 163-167.	1.5	3
10	Modeling the distribution of Ga and Sb impurities in Ge-Si single crystals grown by double feeding of the melt: Growth conditions for homogeneous single crystals. Crystallography Reports, 2016, 61, 327-330.	0.6	3
11	Electron mobility in Ge-like Ge-Si alloys. Solid State Communications, 1992, 84, 445-447.	1.9	2
12	Electroactive complex in thermally treated Ge-Si-Cu, Al crystals. Crystallography Reports, 2010, 55, 462-465.	0.6	2
13	Deep donor center in Ge <sup>1-x</sup> Si <sup>x</sup> -Cu, In, Sb crystals at 1050-1080 K. Inorganic Materials, 2010, 46, 1285-1289.	0.8	2
14	Modeling the concentration profiles of aluminum and indium impurities in crystals of germanium-silicon solid solutions. Inorganic Materials, 2016, 52, 244-247.	0.8	2
15	Growth dynamics of Ge <sup>1-x</sup> Si <sup>x</sup> single crystals obtained by directional constitutional supercooling of the melt. Crystallography Reports, 2011, 56, 531-534.	0.6	1
16	Deep acceptor complex in thermally processed Ge-Si-Ga, Ni crystals. Crystallography Reports, 2014, 59, 563-566.	0.6	0
17	Distribution of Al and in impurities along homogeneous Ge-Si crystals grown by the Czochralski method using Si feeding rod. Crystallography Reports, 2014, 59, 415-417.	0.6	0